

N-channel 40 V, 1.6 mΩ logic level MOSFET in LFPAK56 31 May 2018

#### Product data sheet

#### 1. General description

Automotive qualified N-channel MOSFET using the latest Trench 9 low ohmic superjunction technology, housed in a robust LFPAK56 package. This product has been fully designed and qualified to meet AEC-Q101 requirements delivering high performance and endurance.

### 2. Features and benefits

- Fully automotive qualified to AEC-Q101:
  - 175 °C rating suitable for thermally demanding environments
- Trench 9 Superjunction technology:
  - Reduced cell pitch enables enhanced power density and efficiency with lower R<sub>DSon</sub> in • same footprint
  - Improved SOA and avalanche capability compared to standard TrenchMOS •
  - Tight  $V_{GS(th)}$  limits enable easy paralleling of MOSFETs
- LFPAK Gull Wing leads:
  - · High Board Level Reliability absorbing mechanical stress during thermal cycling, unlike traditional QFN packages
  - Visual (AOI) soldering inspection, no need for expensive x-ray equipment
  - Easy solder wetting for good mechanical solder joint
- LFPAK copper clip technology:
  - Improved reliability, with reduced Rth and RDSon
  - Increases maximum current capability and improved current spreading •

#### 3. Applications

- 12 V automotive systems
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

### 4. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤  T <sub>j</sub> ≤  175 °C		-	-	40	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C	[1]	-	-	120	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	294	W

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		l.	•		
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 10	0.86	1.23	1.6	mΩ
Dynamic ch	naracteristics		l l			_
Q <sub>GD</sub>	gate-drain charge	$I_D$ = 25 A; $V_{DS}$ = 20 V; $V_{GS}$ = 4.5 V; Fig. 12; Fig. 13	-	8.3	16.6	nC
Source-dra	in diode					_
Q <sub>r</sub>	recovered charge	$I_{S}$ = 25 A; dI <sub>S</sub> /dt = -100 A/µs; V <sub>GS</sub> = 0 V;	-	30.6	-	nC
S	softness factor	V <sub>DS</sub> = 20 V; T <sub>j</sub> = 25 °C; <u>Fig. 16</u>	-	0.84	-	

[1] 120A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature

### 5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	a	G
4	G	gate		mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

### 6. Ordering information

Fable 3. Ordering information					
Type number	Package				
	Name	Description	Version		
BUK9Y1R6-40H	LFPAK56; Power-SO8	plastic, single-ended surface-mounted package; 4 terminals	SOT669		

### 7. Marking

Table 4. Marking codes				
	Type number	Marking code		
	BUK9Y1R6-40H	91H640		

### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

BUK9Y1R6-40H

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### BUK9Y1R6-40H

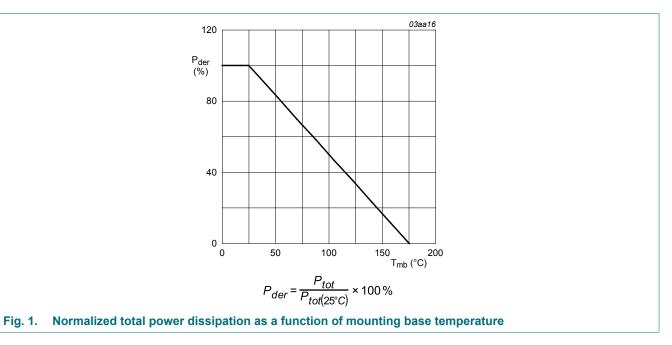
#### N-channel 40 V, 1.6 mΩ logic level MOSFET in LFPAK56

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	40	V
V <sub>GS</sub>	gate-source voltage	DC; T <sub>j</sub> ≤ 175 °C		-10	16	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	294	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C	[1]	-	120	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; Fig. 2		-	600	А
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drain	n diode				·	
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	120	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	600	А
Avalanche r	uggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$\label{eq:ld} \begin{array}{l} I_D = 120 \text{ A};  V_{sup} \leq \mbox{ 40 V};  \text{R}_{GS} = 50 \ \Omega; \\ V_{GS} = 10 \text{ V};  T_{j(init)} = 25 \ ^\circ\text{C}; \mbox{ unclamped}; \\ \hline \mbox{ Fig. 3 } \end{array}$	[2] [3]	-	158	mJ

[1] 120A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature

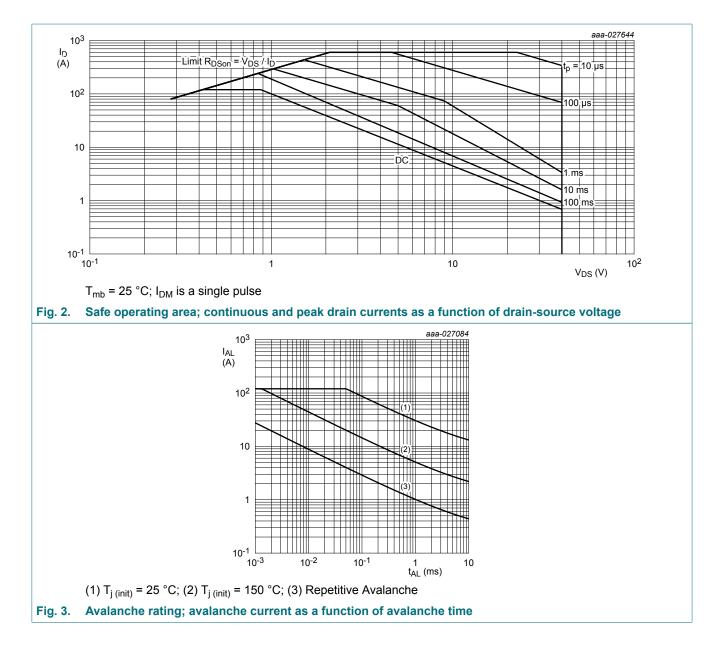
[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C

[3] Refer to application note AN10273 for further information



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#### 9. Thermal characteristics

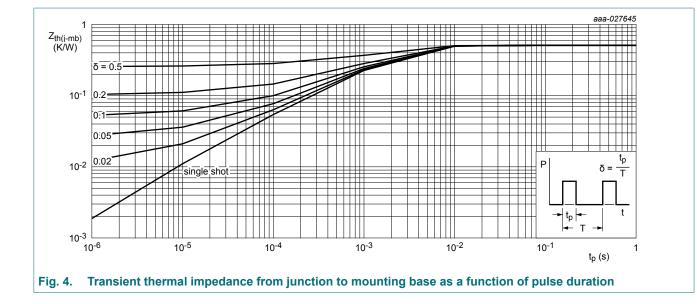
#### Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	<u>Fig. 4</u>	-	0.39	0.51	K/W

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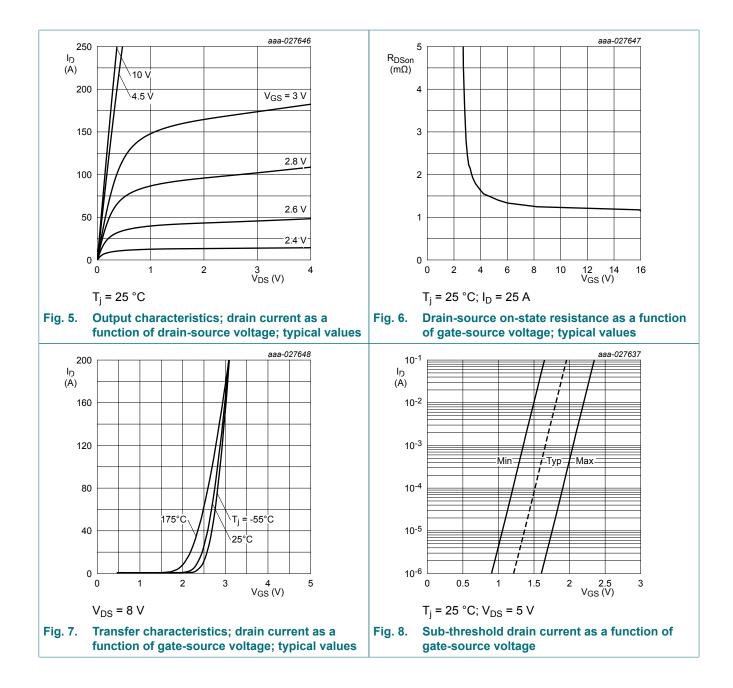
#### **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · ·				
V <sub>(BR)DSS</sub>	drain-source	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	40	43	-	V
	breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -40 °C	-	40.5	-	V
		I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C	36	40	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C; <u>Fig. 8</u> ; Fig. 9	1.35	1.62	2.05	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; <u>Fig. 9</u>	0.6	-	-	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = -55 °C; <u>Fig. 9</u>	-	-	2.5	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.11	5	μA
		V <sub>DS</sub> = 16 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C	-	1.8	10	μA
		V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	220	500	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	2	100	nA

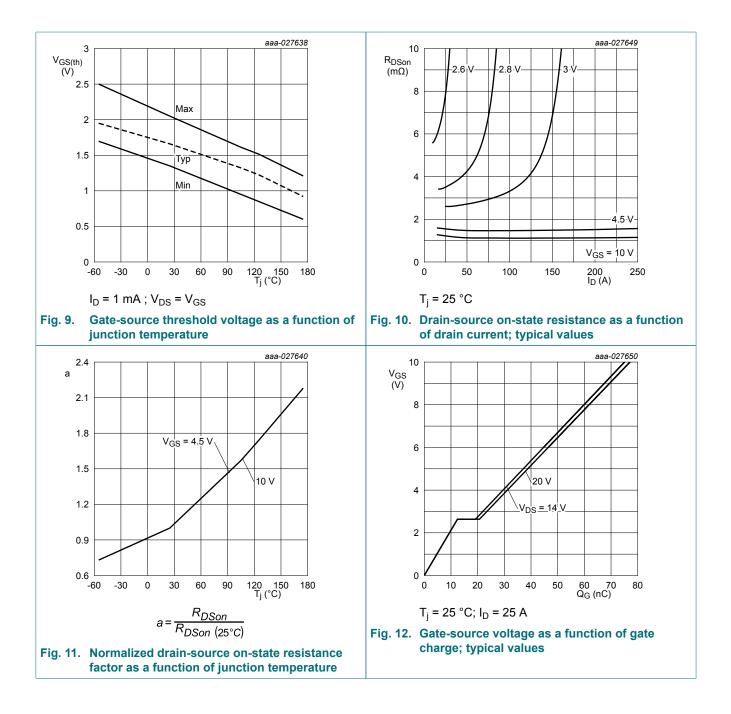
#### N-channel 40 V, 1.6 m $\Omega$ logic level MOSFET in LFPAK56

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	0.86	1.23	1.6	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 105 °C; <u>Fig. 11</u>	1.3	1.89	2.5	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 125 °C; <u>Fig. 11</u>	1.4	2.08	2.8	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; <u>Fig. 11</u>	1.8	2.62	3.5	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	1.1	1.55	2.2	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 105 °C; <u>Fig. 11</u>	1.6	2.34	3.5	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 125 °C; Fig. 11	1.8	2.57	3.8	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; <u>Fig. 11</u>	2.3	3.21	4.8	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz; T <sub>j</sub> = 25 °C	0.36	0.9	2.25	Ω
Dynamic cl	haracteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D$ = 25 A; $V_{DS}$ = 20 V; $V_{GS}$ = 10 V; Fig. 12; Fig. 13	-	77	107.8	nC
		$I_D = 25 \text{ A}; V_{DS} = 20 \text{ V}; V_{GS} = 4.5 \text{ V};$ Fig. 12; Fig. 13	-	34.9	48.9	nC
Q <sub>GS</sub>	gate-source charge		-	12.4	18.6	nC
Q <sub>GD</sub>	gate-drain charge		-	8.3	16.6	nC
C <sub>iss</sub>	input capacitance	Fig. 12; Fig. 13 V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	-	5402	7563	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 14</u>	-	1022	1431	pF
C <sub>rss</sub>	reverse transfer capacitance		-	208	458	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 20 V; R <sub>L</sub> = 0.8 Ω; V <sub>GS</sub> = 4.5 V;	-	27.6	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega$	-	30.3	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	39.4	-	ns
t <sub>f</sub>	fall time	1 1	-	22.9	-	ns
Source-dra	in diode		I			1
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C; <u>Fig. 15</u>	-	0.8	1.2	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 25 A; dI <sub>S</sub> /dt = -100 A/µs; V <sub>GS</sub> = 0 V;	-	34.7	-	ns
Qr	recovered charge	V <sub>DS</sub> = 20 V; T <sub>j</sub> = 25 °C; <u>Fig. 16</u>	-	30.6	-	nC
S	softness factor	1 1	-	0.84	-	1
		$I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -500 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V}; \\ \text{V}_{DS} = 20 \text{ V}; \text{ T}_{j} = 25 \text{ °C}; \text{ Fig. 16}$	-	0.66	-	

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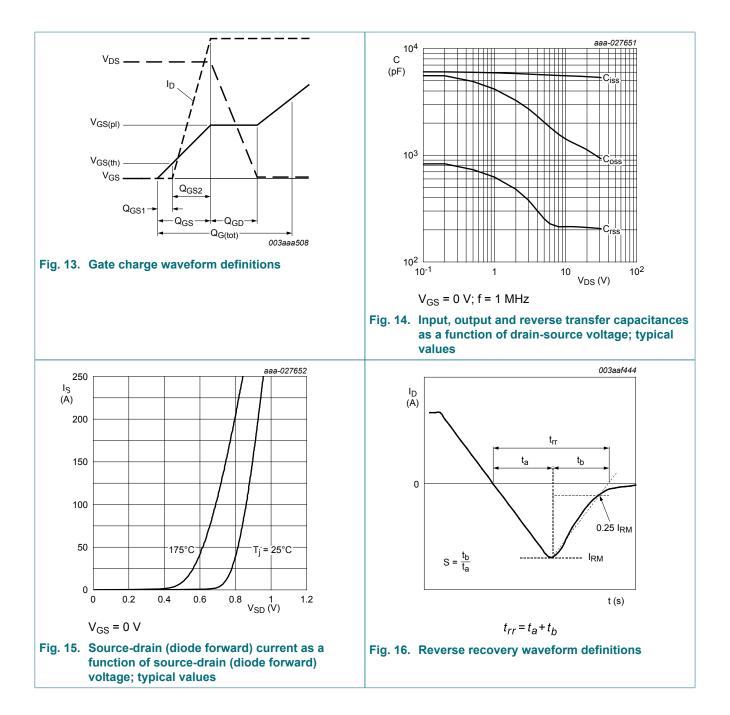


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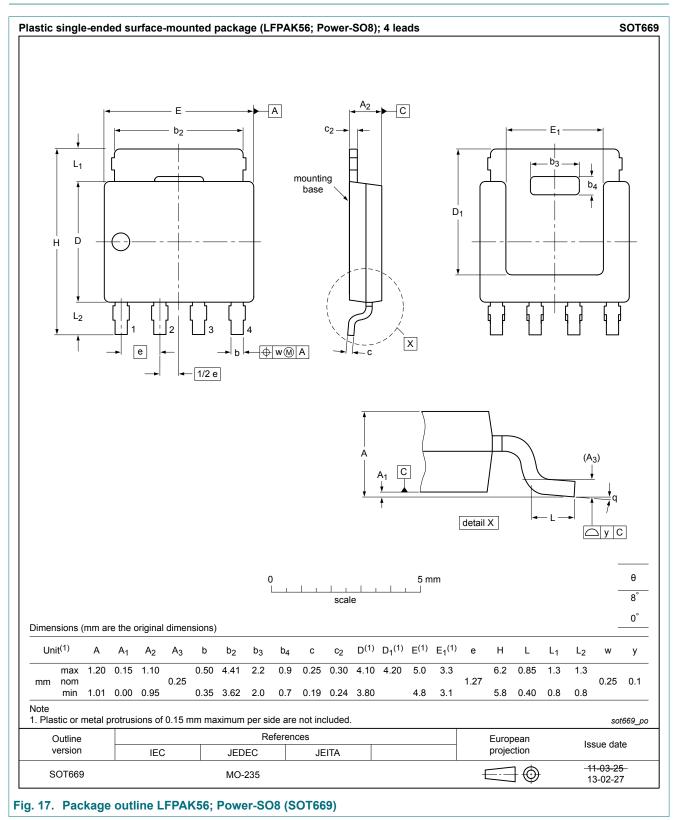
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#### N-channel 40 V, 1.6 m $\Omega$ logic level MOSFET in LFPAK56



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#### 11. Package outline



BUK9Y1R6-40H

#### N-channel 40 V, 1.6 mΩ logic level MOSFET in LFPAK56

#### 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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#### N-channel 40 V, 1.6 mΩ logic level MOSFET in LFPAK56

### Contents

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	2
8.	Limiting values	2
9.	Thermal characteristics	4
10.	Characteristics	5
11.	Package outline1	0
12.	Legal information1	1

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